MOS FET

FK4B01100L

Panasonic

FK4B01100L

Single N-channel MOS FET

For load switching circuits

■ Features

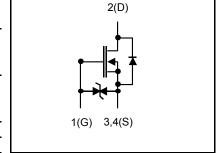
- Low Drain-source ON resistance:RDS(on) typ. = 27 m Ω (VGS = 2.5 V)
- CSP (Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)
- Marking Symbol: 1A

■ Packaging

Embossed type (Thermo-compression sealing): 20 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit				
Drain-Source Voltage	VDS	12	V				
Gate-Source Voltage	VGS	±8	V				
	ID1 ^{*1}	3.4					
Drain Current	ID2*2	5.2	Α				
	ID3 ^{*3}	6.5					
Peak Drain Current	IDp1*1*4	27					
	IDp2*2*4	41	Α				
	IDp3 ^{*3*4}	52					
	PD1 ^{*1}	0.36	W				
Power Dissipation	PD2 ^{*2}	0.82					
	PD3 ^{*3}	1.3					
Channel Temperature	Tch	150	°C				
Operating Ambient Temperature	Topr	-40 ~ +85	°C				
Storage Temperature	Tstg	-55 ~ +150	°C				
N + #4 FD4 + 1/05 4							



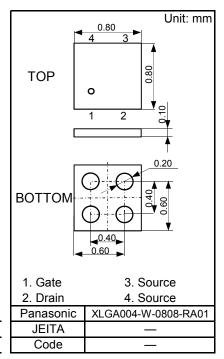
■ Internal Connection

- Note *1 FR4 board (25.4mm×25.4mm×t1.0mm), Min Cu 36mm² Copper
 - *2 FR4 board (25.4mm×25.4mm×t1.0mm), Full Cu
 - *3 Ceramic substrate (70mm×70mm×t1.0mm)
 - *4 $t = 10 \mu s$, Duty Cycle < 1%

Established: 2014-03-24

: 2014-12-15

Revised



MOS FET

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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0	12			V
Zero Gate Voltage Drain Current	IDSS	VDS = 12 V, VGS = 0			10	μΑ
Gate-Source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA
Gate Threshold Voltage	Vth	ID = 236 μA, VDS =10 V	0.3		1.0	V
Drain-Source ON Resistance	RDS(on)	ID = 1.5 A, VGS = 4.5 V		22	30	mΩ
		ID = 1.0 A, VGS = 2.5 V		27	40	
		ID = 0.5 A, VGS = 1.8 V		33	56	
		ID = 0.25 A, VGS = 1.5 V		43	99	
Input Capacitance *1	Ciss	VDS = 10 V		275		
Output Capacitance *1	Coss	VGS = 0		100		pF
Reverse Transfer Capacitance *1	Crss	f = 1MHz		70		
Turn-on delay time *1,*2	td(on)	VDD = 6 V		7		
Rise time *1,*2	tr	VGS = 0 to 4.5 V		14		ns
Turn-off delay time *1,*2	td(off)	ID=1.0 A		165		
Fall time *1,*2	tf	110-1:0 A		76		
Total Gate Charge *1	Qg	VDD = 6 V		5.8		nC
Gate to Source Charge *1	Qgs	VGS = 4.5 V		0.75		nC
Gate to Drain Miller Charge *1	Qgd	IS= 1.0 A		0.95		nC
Body Diode Forward Voltage	VF(D-S)	IF = 0.2A, VGS = 0V		0.6	1.2	V

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

■ Electrical State Discharge Characteristics

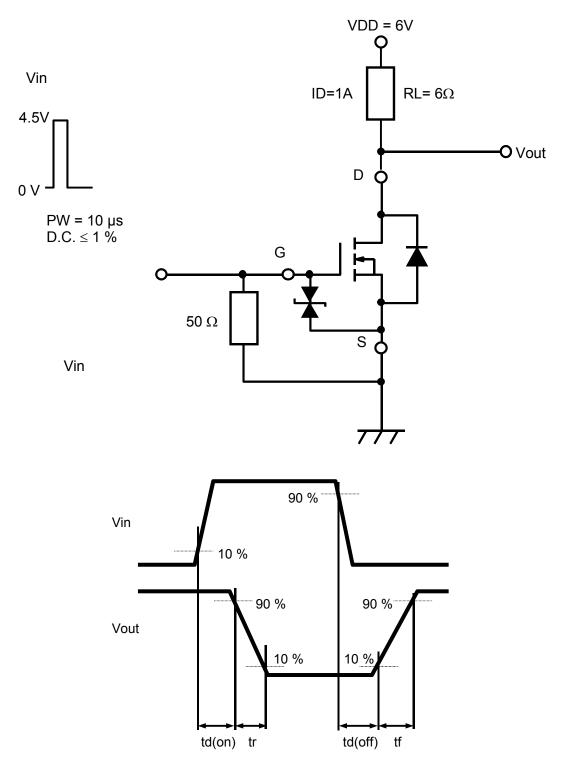
Standard	Test Type	Symbol	Conditions	Class	Valu	е	Unit
AEC-Q101-001	Human body model	HBM	C = 100 pF, R = 1.5 k Ω	H1C	>1k to	2k	V
	Machine model	MM	C = 200 pF, R = 0 Ω	M2	>100 to	200	V

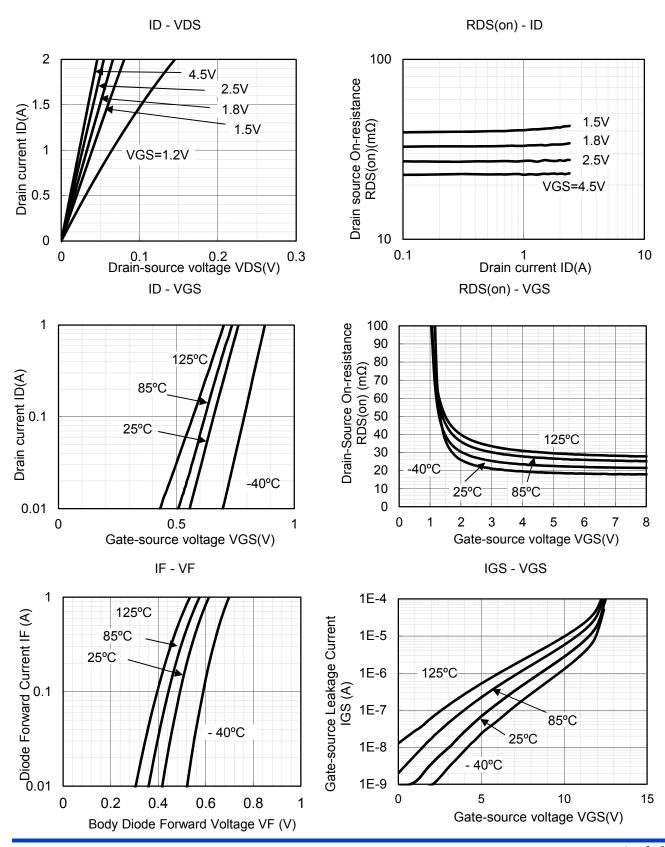
^{*1} Guaranteed by design, not subject to production testing

^{*2} Measurement circuit for Turn-on delay time / Rise time / Turn-off delay time / Fall time

Established: 2014-03-24 Revised: 2014-12-15

Note2: Measurement circuit

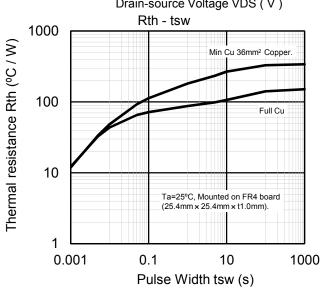




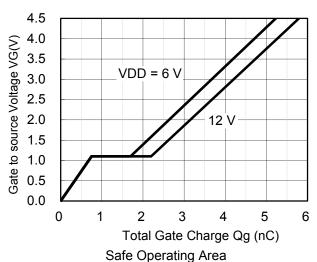
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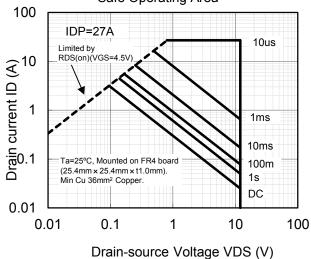
IDS - VDS

1E-3 Zero Gate Voltage Drain Current 1E-4 1E-5 125°C 1E-6 IDS(A) 1E-7 85°C 1E-8 25°C 1E-9 1E-10 -40°C 1E-11 0 5 10 15 20 25 Drain-source Voltage VDS (V)



Dynamic Input/Output Characteristics

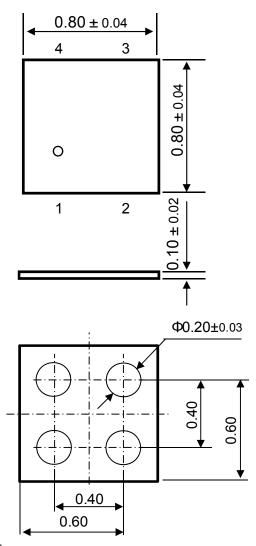




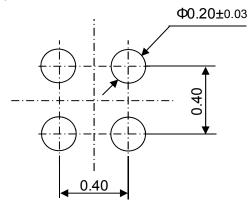
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■ XLGA004-W-0808-RA01

Unit: mm



■ Land Pattern (Reference)



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